

General Description

The WSM340N10G is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications.

The WSM340N10G meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

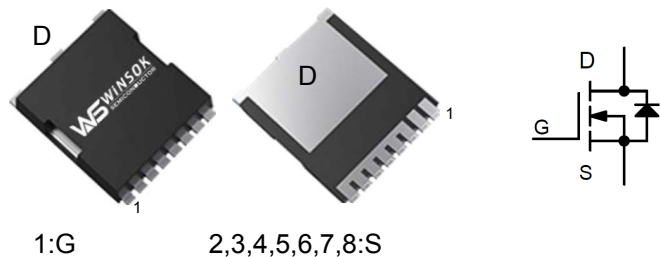
Product Summary

BV _{DSS}	R _{DS(on)}	I _D
100V	1.6mΩ	300A

Applications

synchronous rectification
DC/DC Converter
Load switch.

TOLL Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V	300	A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V	230	A
I _{DM}	Pulsed Drain Current T _C =25°C	1150	A
EAS	Avalanche Energy, Single pulse, L=0.5mH	1800	mJ
I _{AS}	Avalanche Current, Single pulse, L=0.5mH	120	A
P _D @T _C =25°C	Total Power Dissipation	375	W
P _D @T _C =100°C	Total Power Dissipation	187	W
T _{STG}	Storage Temperature Range	-55 to 175	°C
T _J	Operating Junction Temperature Range	175	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient	---	50	°C/W
R _{θJC}	Thermal Resistance Junction-Case	---	0.4	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.096	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =50A	---	1.6	2.3	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250μA	2.0	3.0	4.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.5	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =85V, V _{GS} =0V, T _J =25°C	---	---	1	μA
		V _{DS} =85V, V _{GS} =0V, T _J =55°C	---	---	10	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±25V, V _{DS} =0V	---	---	±100	nA
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.0	---	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =50V, V _{GS} =10V, I _D =50A	---	260	---	nC
Q _{gs}	Gate-Source Charge		---	80	---	
Q _{gd}	Gate-Drain Charge		---	60	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =50V, V _{GS} =10V, R _G =1Ω, R _L =1Ω, I _{DS} =1A.	---	88	---	ns
T _r	Rise Time		---	50	---	
T _{d(off)}	Turn-Off Delay Time		---	228	---	
T _f	Fall Time		---	322	---	
C _{iss}	Input Capacitance	V _{DS} =40V, V _{GS} =0V, f=1MHz	---	13900	---	pF
C _{oss}	Output Capacitance		---	6160	---	
C _{rss}	Reverse Transfer Capacitance		---	220	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	160	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =50A, T _J =25°C	---	---	1.2	V

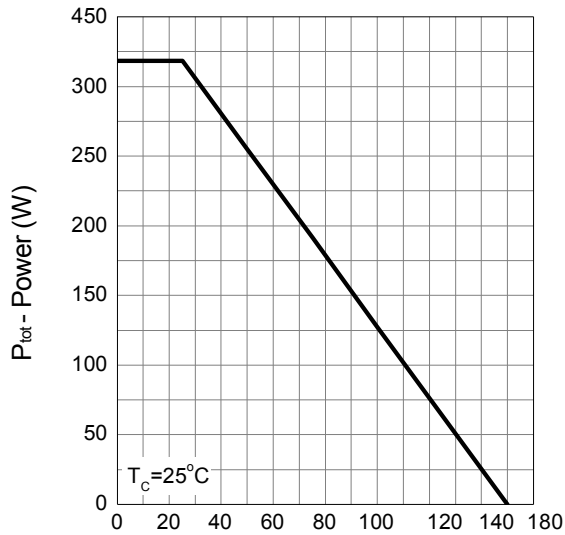
A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t_s 10s junction to ambient thermal resistance rating.

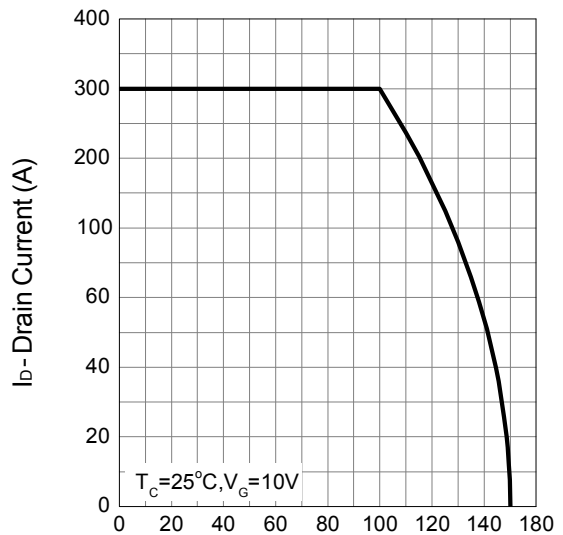
Typical Operating Characteristics

Power Dissipation



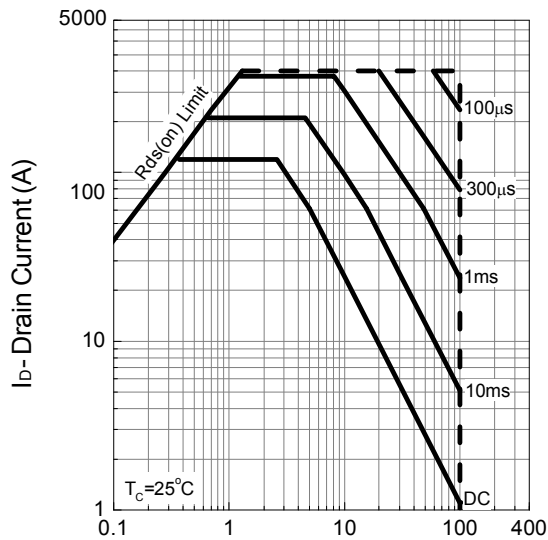
T_j - Junction Temperature ($^\circ C$)

Drain Current



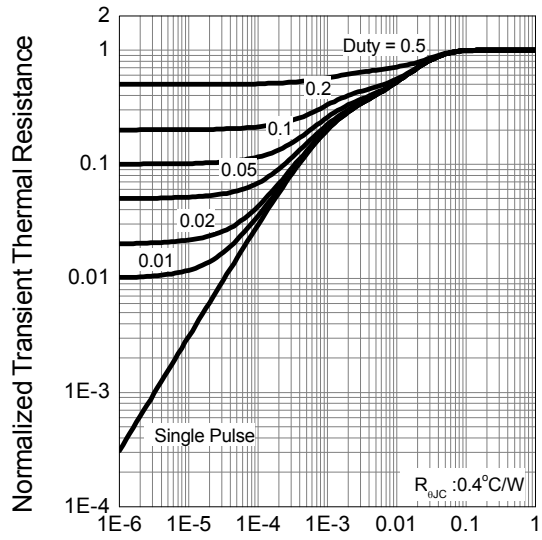
T_j - Junction Temperature ($^\circ C$)

Safe Operation Area



V_{DS} - Drain - Source Voltage (V)

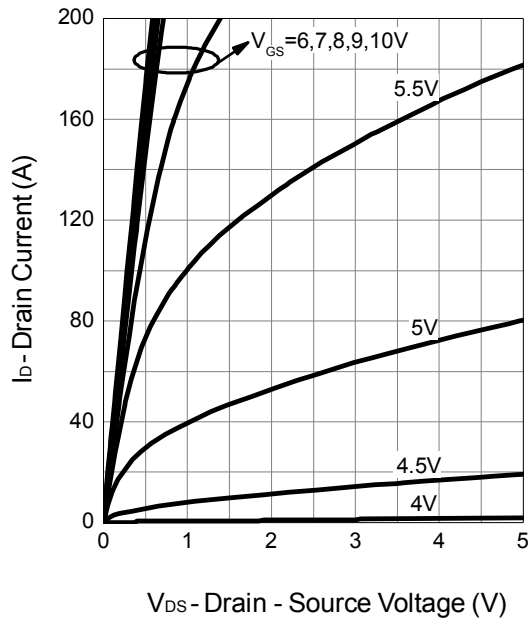
Thermal Transient Impedance



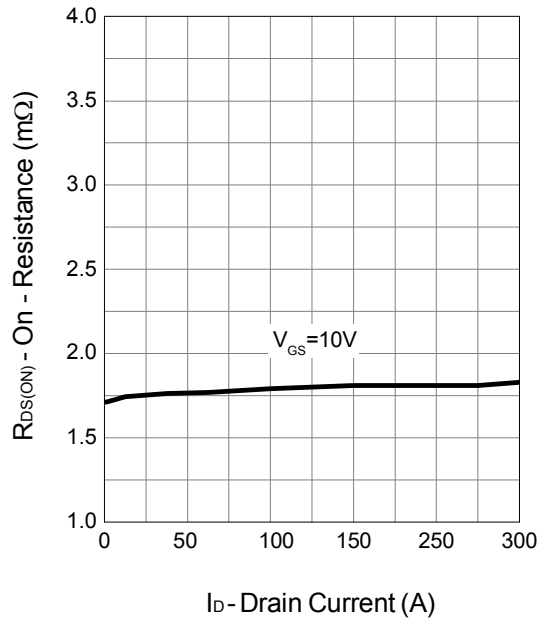
Square Wave Pulse Duration (sec)

Typical Operating Characteristics

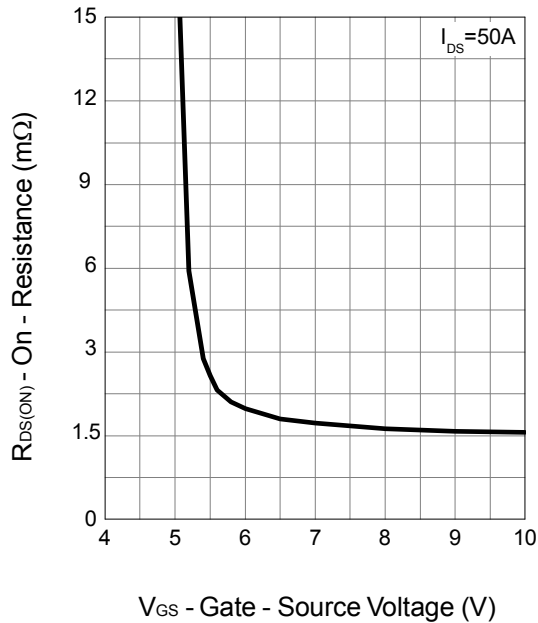
Output Characteristics



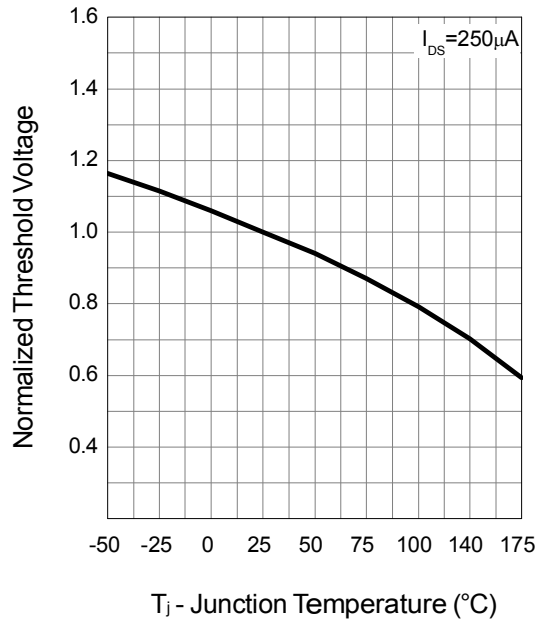
Drain-Source On Resistance



Gate-Source On Resistance

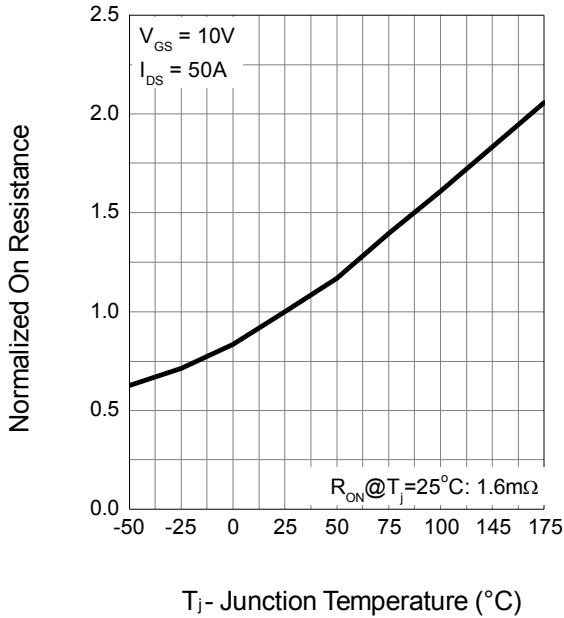


Gate Threshold Voltage

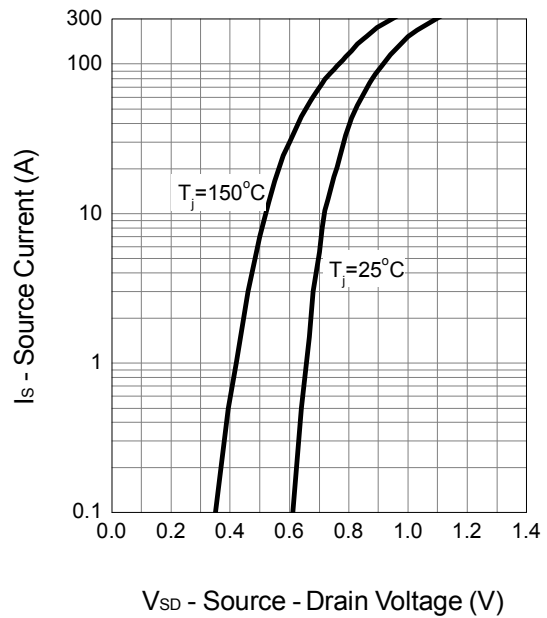


Typical Operating Characteristics

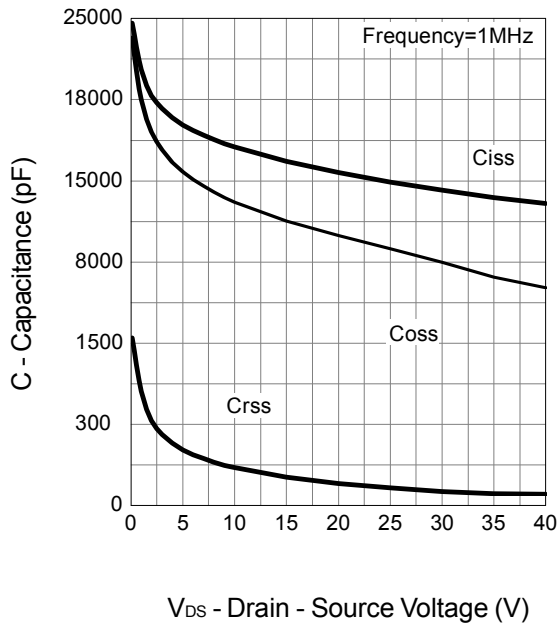
Drain-Source On Resistance



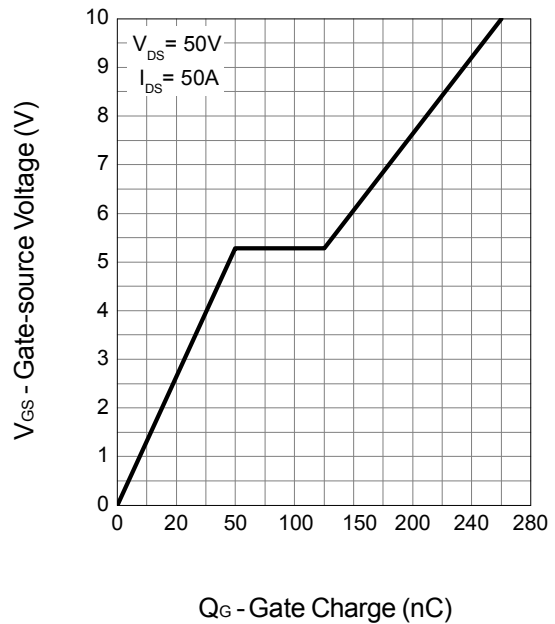
Source-Drain Diode Forward



Capacitance



Gate Charge





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